

RMLV3216A Series

32Mb Advanced LPSRAM (2M word × 16bit / 4M word × 8bit)

R10DS0277EJ0200
Rev.2.00
2024.04.24

Description

The RMLV3216A Series is a family of 32-Mbit static RAMs organized 2,097,152-word × 16-bit, fabricated by Renesas's high-performance Advanced LPSRAM technologies. The RMLV3216A Series has realized higher density, higher performance and low power consumption. The RMLV3216A Series offers low power standby power dissipation; therefore, it is suitable for battery backup systems. It is offered in 48pin TSOP (I), 52pin μTSOP (II) or 48-ball fine pitch ball grid array.

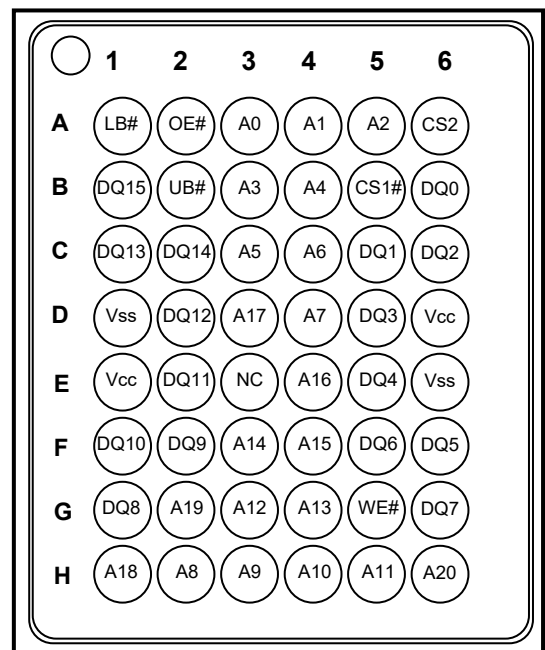
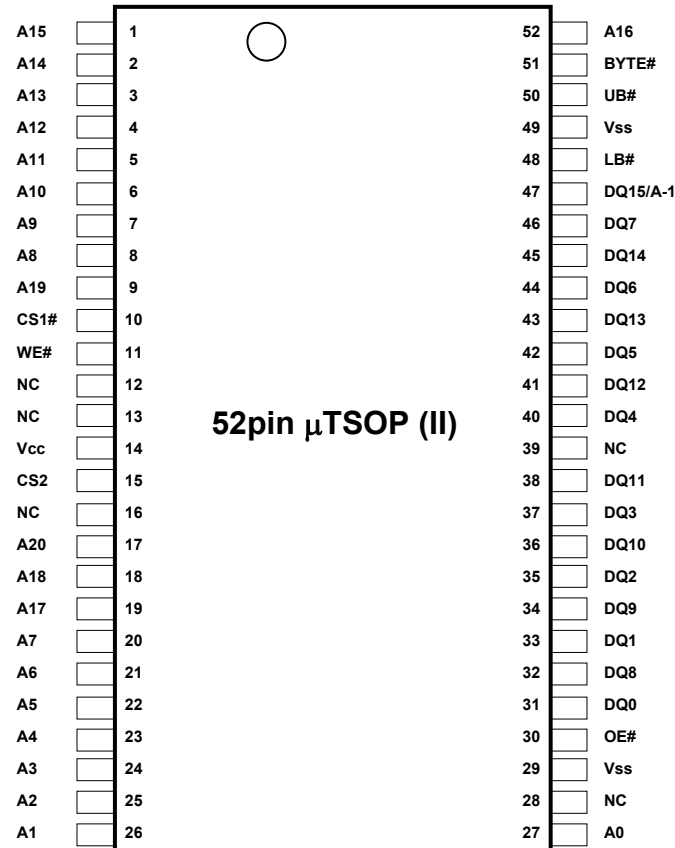
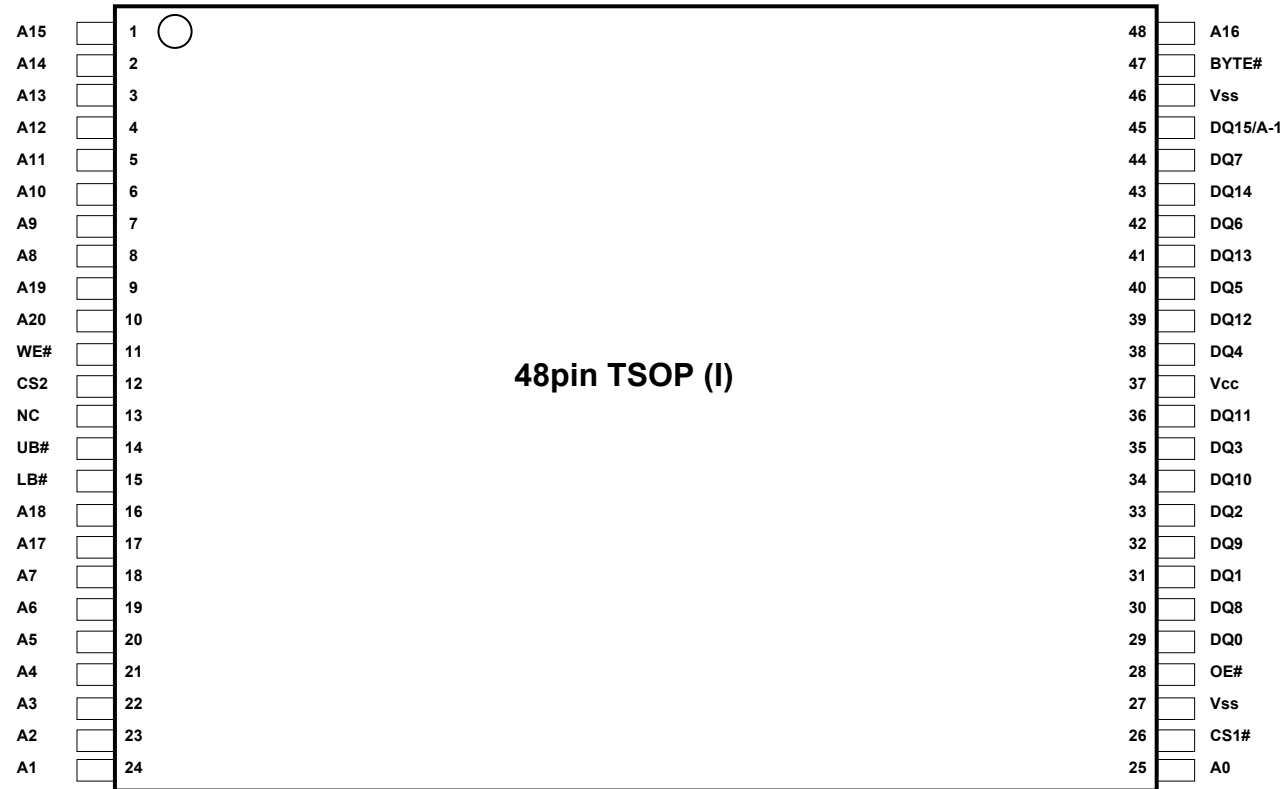
Features

- Single 3V supply: 2.7V to 3.6V
- Access time: 55ns (max.)
- Current consumption:
 - Standby: 0.6μA (typ.)
- Common data input and output
 - Three state output
- Directly TTL compatible
 - All inputs and outputs
- Battery backup operation

Part Name Information

Part Name	Access time	Temperature Range	Package
RMLV3216AGSA-5S2	55 ns	-40 ~ +85°C	12mm x 20mm 48pin plastic TSOP (I)
RMLV3216AGSD-5S2			10.79mm × 10.49mm 52pin plastic μTSOP (II)
RMLV3216AGBG-5S2			48-ball FBGA with 0.75mm ball pitch

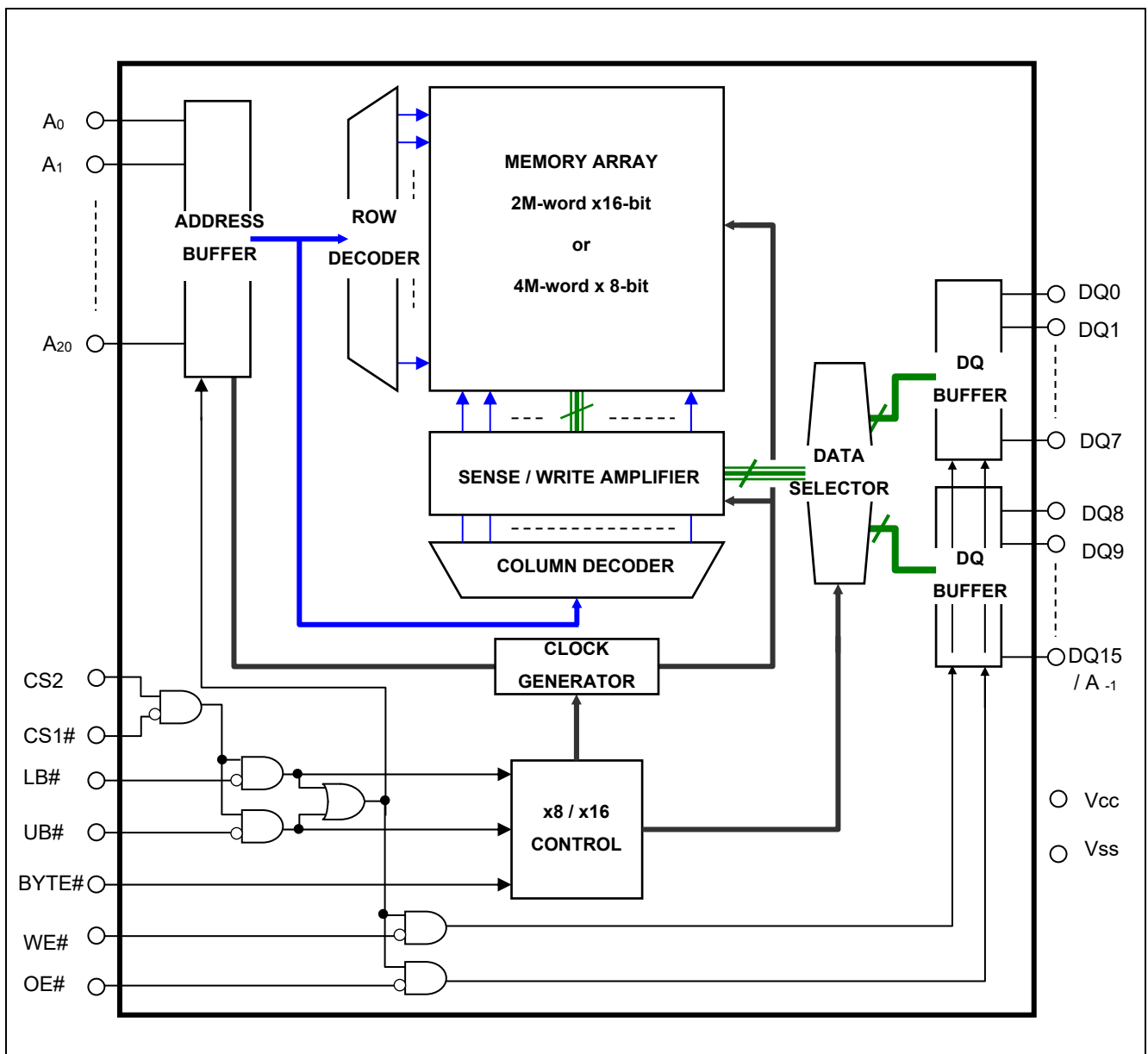
Pin Arrangement



Pin Description

Pin name	Function
V _{CC}	Power supply
V _{SS}	Ground
A0 to A20	Address input (word mode)
A-1 to A20	Address input (byte mode)
DQ0 to DQ15	Data input/output
CS1#	Chip select 1
CS2	Chip select 2
OE#	Output enable
WE#	Write enable
LB#	Lower byte select
UB#	Upper byte select
BYTE#	Byte control mode enable
NC	No connection

Block Diagram



Note 1. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

Operation Table

CS1#	CS2	BYTE#	UB#	LB#	WE#	OE#	DQ0~7	DQ8~14	DQ15	Operation
H	X	X	X	X	X	X	High-Z	High-Z	High-Z	Stand-by
X	L	X	X	X	X	X	High-Z	High-Z	High-Z	Stand-by
X	X	H	H	H	X	X	High-Z	High-Z	High-Z	Stand-by
L	H	H	H	L	L	X	Din	High-Z	High-Z	Write in lower byte
L	H	H	H	L	H	L	Dout	High-Z	High-Z	Read in lower byte
L	H	H	H	L	H	H	High-Z	High-Z	High-Z	Output disable
L	H	H	L	H	L	X	High-Z	Din	Din	Write in upper byte
L	H	H	L	H	H	L	High-Z	Dout	Dout	Read in upper byte
L	H	H	L	H	H	H	High-Z	High-Z	High-Z	Output disable
L	H	H	L	L	L	X	Din	Din	Din	Word write
L	H	H	L	L	H	L	Dout	Dout	Dout	Word read
L	H	H	L	L	H	H	High-Z	High-Z	High-Z	Output disable
L	H	L	X	X	L	X	Din	High-Z	A-1	Byte write
L	H	L	X	X	H	L	Dout	High-Z	A-1	Byte read
L	H	L	X	X	H	H	High-Z	High-Z	A-1	Output disable

Note 2. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

3. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.
48-ball FBGA type equals BYTE#=H mode.

Absolute Maximum Ratings

Parameter	Symbol	Value	unit
Power supply voltage relative to V_{SS}	V_{CC}	-0.5 to +4.6	V
Terminal voltage on any pin relative to V_{SS}	V_T	-0.5 ⁴ to $V_{CC}+0.3$ ⁵	V
Power dissipation	P_T	0.7	W
Operation temperature	T_{opr}	-40 to +85	°C
Storage temperature range	T_{stg}	-65 to +150	°C
Storage temperature range under bias	T_{bias}	-40 to +85	°C

Note 4. -2.0V for pulse ≤ 30 ns (full width at half maximum)

5. Maximum voltage is +4.6V.

DC Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note
Supply voltage	V_{CC}	2.7	3.0	3.6	V	
	V_{SS}	0	0	0	V	
Input high voltage	V_{IH}	2.2	—	$V_{CC}+0.3$	V	
Input low voltage	V_{IL}	-0.3	—	0.6	V	6
Ambient temperature range	T_a	-40	—	+85	°C	

Note 6. -2.0V for pulse ≤ 30 ns (full width at half maximum)

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions ^{*7}	
Input leakage current	I _{LI}	—	—	1	μA	V _{in} = V _{SS} to V _{CC}	
Output leakage current	I _{LO}	—	—	1	μA	CS1# = V _{IH} or CS2 = V _{IL} or OE# = V _{IH} or WE# = V _{IL} or LB# = UB# = V _{IH} , V _{I/O} = V _{SS} to V _{CC}	
Average operating current	I _{CC1}	—	27 ^{*8}	35	mA	Cycle = 55ns, duty = 100%, I _{I/O} = 0mA, CS1# = V _{IL} , CS2 = V _{IH} , Others = V _{IH} /V _{IL}	
	I _{CC2}	—	2 ^{*8}	4	mA	Cycle = 1μs, duty = 100%, I _{I/O} = 0mA, CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V	
Standby current	I _{SB}	—	0.1 ^{*8}	0.3	mA	CS2 = V _{IL} , Others = V _{SS} to V _{CC}	
Standby current	I _{SB1}	—	0.6 ^{*8}	4	μA	~+25°C	V _{in} = V _{SS} to V _{CC} , (1) CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V or (3) LB# = UB# ≥ V _{CC} -0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V
		—	1 ^{*9}	6	μA	~+40°C	
		—	4 ^{*10}	12	μA	~+70°C	
		—	8 ^{*11}	18	μA	~+85°C	
Output high voltage	V _{OH}	2.4	—	—	V	I _{OH} = -1mA	
Output low voltage	V _{OL}	—	—	0.4	V	I _{OL} = 2mA	

Note 7. BYTE# pin supported by only 48pin TSOP (I) and 52pin μTSOP (II) types.
 BYTE# $\geq V_{CC} - 0.2\text{V}$ or BYTE# $\leq 0.2\text{V}$

8. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=25^{\circ}\text{C}$), and not 100% tested.
 9. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=40^{\circ}\text{C}$), and not 100% tested.
 10. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=70^{\circ}\text{C}$), and not 100% tested.
 11. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=85^{\circ}\text{C}$), and not 100% tested.

Capacitance

(Ta = 25°C, f = 1MHz)

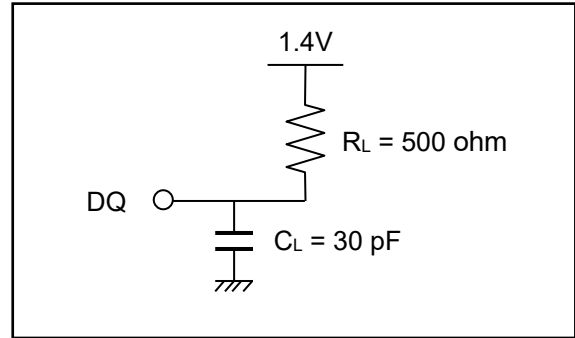
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C in	—	—	10	pF	$V_{in} = 0\text{V}$	12
Input / output capacitance	C I/O	—	—	10	pF	$V_{I/O} = 0\text{V}$	12

Note 12. This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions ($V_{CC} = 2.7V \sim 3.6V$, $T_a = -40 \sim +85^{\circ}C$)

- Input pulse levels:
 $V_{IL} = 0.4V$, $V_{IH} = 2.4V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Read Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Read cycle time	t_{RC}	55		ns	
Address access time	t_{AA}	—	55	ns	
Chip select access time	t_{ACS1}	—	45	ns	
	t_{ACS2}	—	45	ns	
Output enable to output valid	t_{OE}	—	22	ns	
Output hold from address change	t_{OH}	10	—	ns	
LB#, UB# access time	t_{BA}	—	45	ns	
Chip select to output in low-Z	t_{CLZ1}	10	—	ns	13,14
	t_{CLZ2}	10	—	ns	13,14
LB#, UB# enable to low-Z	t_{BLZ}	5	—	ns	13,14
Output enable to output in low-Z	t_{OLZ}	5	—	ns	13,14
Chip deselect to output in high-Z	t_{CHZ1}	0	18	ns	13,14,15
	t_{CHZ2}	0	18	ns	13,14,15
LB#, UB# disable to high-Z	t_{BHZ}	0	18	ns	13,14,15
Output disable to output in high-Z	t_{OHZ}	0	18	ns	13,14,15

Note 13. This parameter is sampled and not 100% tested.

14 At any given temperature and voltage condition, t_{CHZ1} max is less than t_{CLZ1} min, t_{CHZ2} max is less than t_{CLZ2} min, t_{BHZ} max is less than t_{BLZ} min, and t_{OHZ} max is less than t_{OLZ} min, for any device.

15. t_{CHZ1} , t_{CHZ2} , t_{BHZ} and t_{OHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

Write Cycle

Parameter	Symbol	Min.	Max.	Unit	Note
Write cycle time	t_{WC}	55	—	ns	
Address valid to write end	t_{AW}	35	—	ns	
Chip select to write end	t_{CW}	35	—	ns	
Write pulse width	t_{WP}	35	—	ns	16
LB#,UB# valid to write end	t_{BW}	35	—	ns	
Address setup time to write start	t_{AS}	0	—	ns	
Write recovery time from write end	t_{WR}	0	—	ns	
Data to write time overlap	t_{DW}	25	—	ns	
Data hold from write end	t_{DH}	0	—	ns	
Output enable from write end	t_{OW}	5	—	ns	17
Output disable to output in high-Z	t_{OHZ}	0	18	ns	17,18
Write to output in high-Z	t_{WHZ}	0	18	ns	17,18

Note 16. t_{WP} is the interval between write start and write end.

A write starts when all of (CS1#), (CS2), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

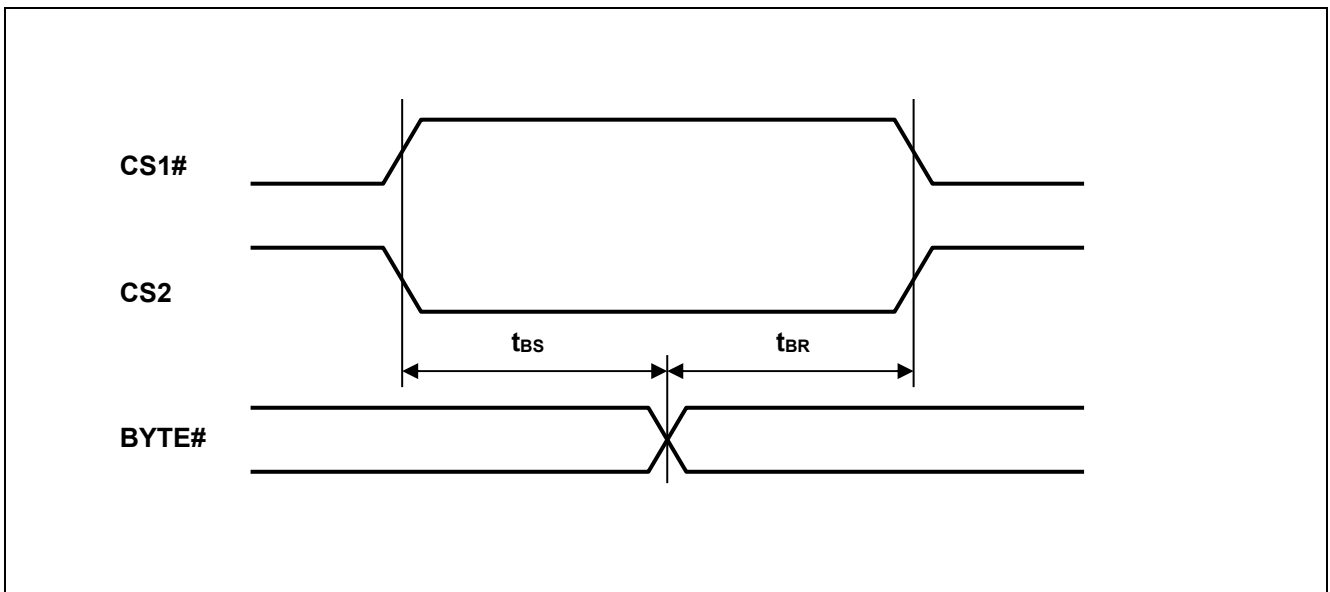
A write ends when any of (CS1#), (CS2), (WE#) or (one or both of LB# and UB#) becomes inactive.

17. This parameter is sampled and not 100% tested.

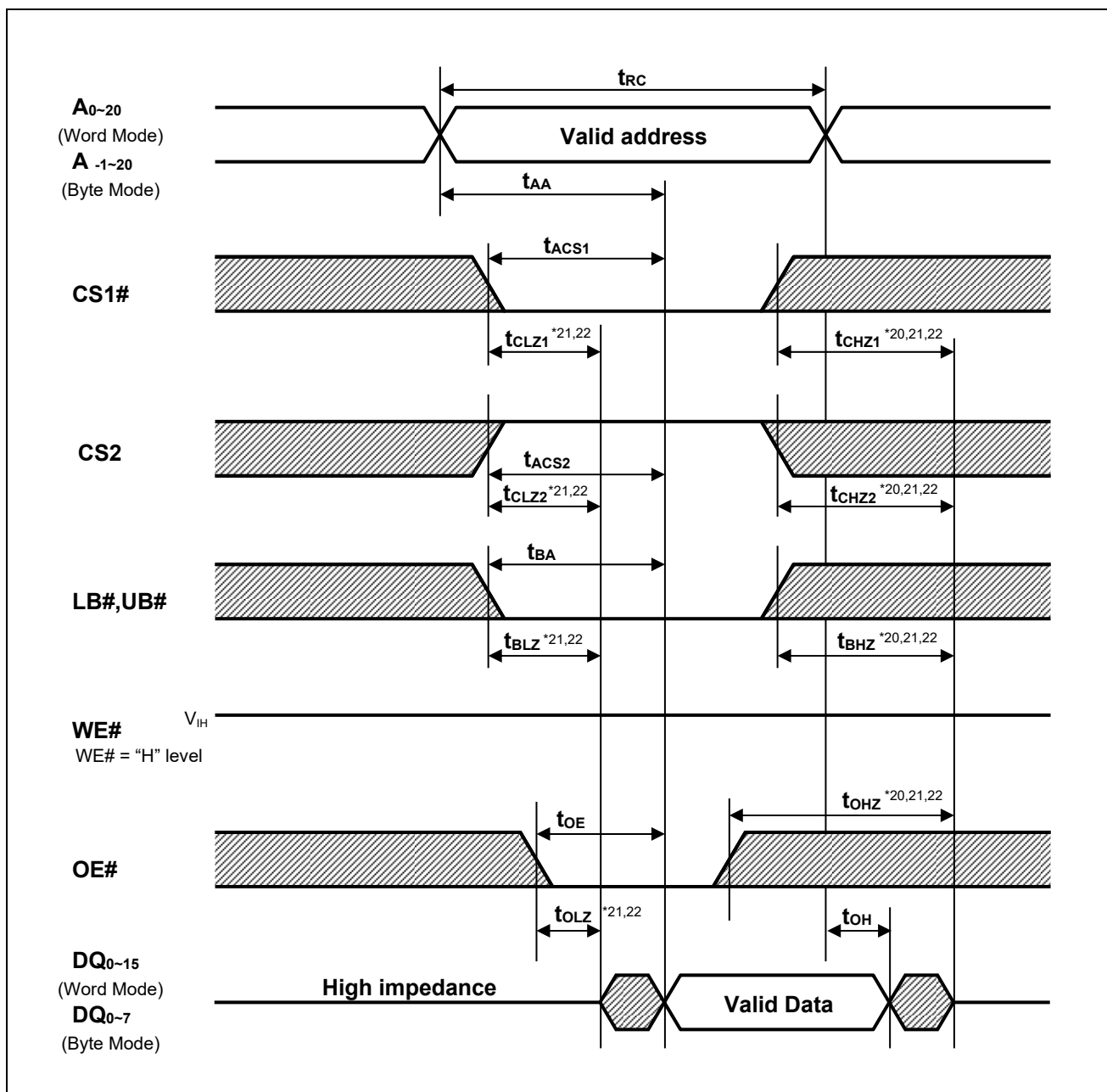
18. t_{OHZ} and t_{WHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

BYTE# Timing Conditions (BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types)

Parameter	Symbol	Min.	Max.	Unit	Note
Byte setup time	t_{BS}	5	-	ms	
Byte recovery time	t_{BR}	5	-	ms	

BYTE# Timing Waveforms


Timing Waveforms

Read Cycle^{*19}

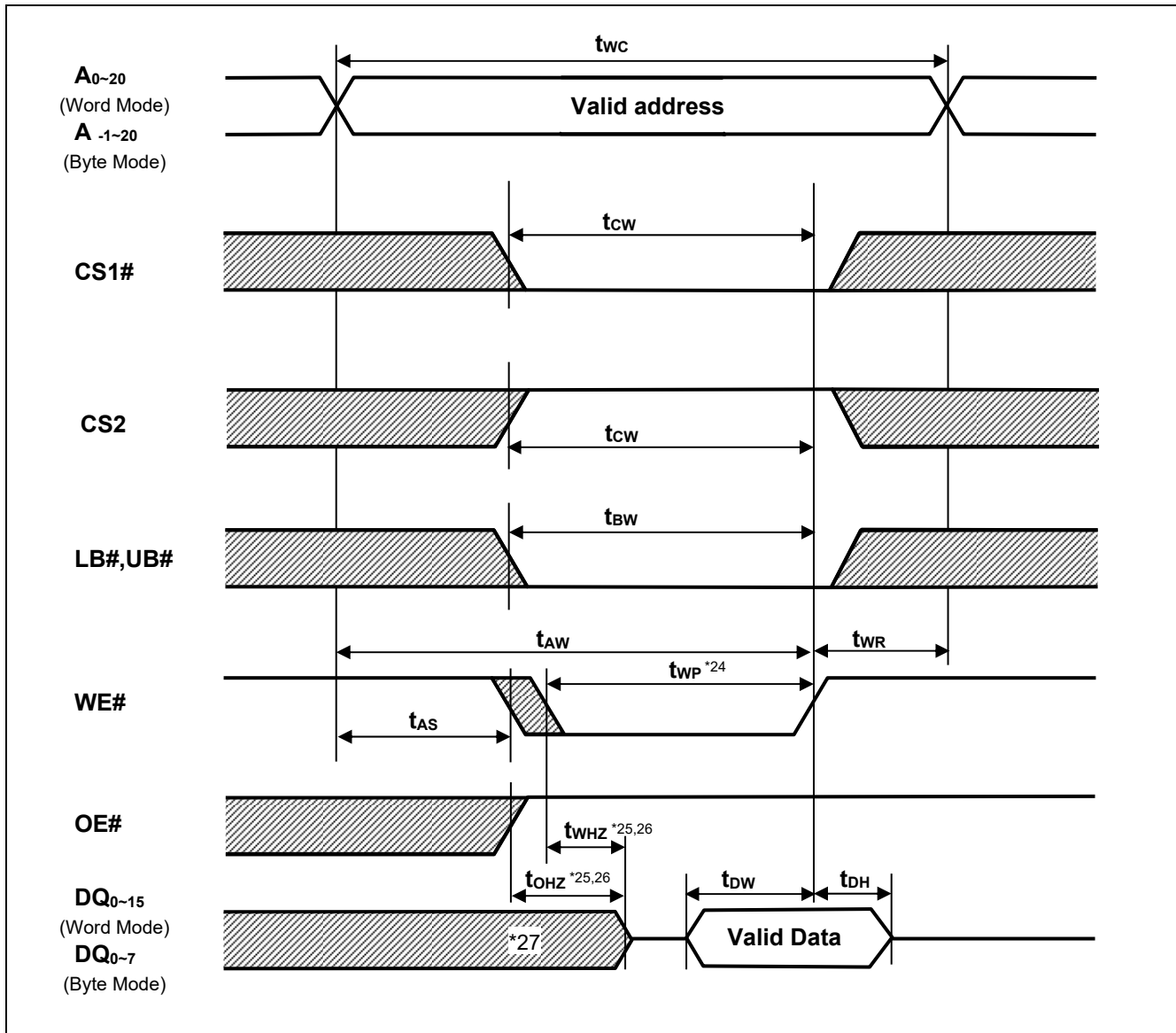
Note 19. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

BYTE# $\geq V_{CC} - 0.2V$ (Word mode) or BYTE# $\leq 0.2V$ (Byte mode)

20. t_{CHZ1} , t_{CHZ2} , t_{BHZ} and t_{OHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

21. This parameter is sampled and not 100% tested.

22. At any given temperature and voltage condition, t_{CHZ1} max is less than t_{CLZ1} min, t_{CHZ2} max is less than t_{CLZ2} min, t_{BHZ} max is less than t_{BLZ} min, and t_{OHZ} max is less than t_{OLZ} min, for any device.

Write Cycle (1)^{*23} (WE# CLOCK, OE#="H" while writing)

Note 23. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

BYTE# $\geq V_{CC} - 0.2V$ (Word mode) or BYTE# $\leq 0.2V$ (Byte mode)

24. t_{WP} is the interval between write start and write end.

A write starts when all of (CS1#), (CS2), (WE#) and (one or both of LB# and UB#) become active.

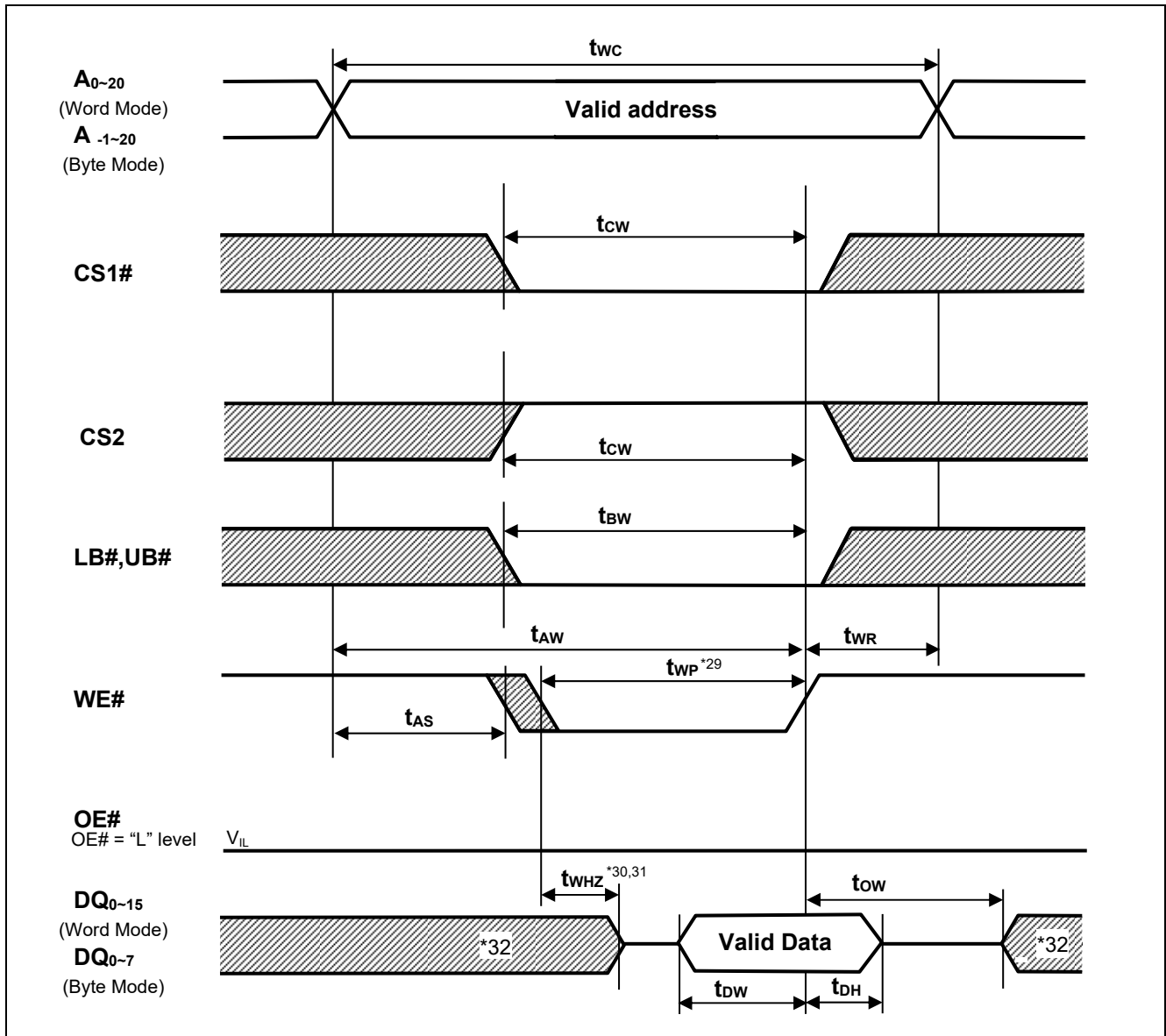
A write is performed during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

A write ends when any of (CS1#), (CS2), (WE#) or (one or both of LB# and UB#) becomes inactive.

25. t_{OHZ} and t_{WHZ} are defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

26. This parameter is sampled and not 100% tested.

27. During this period, DQ pins are in the output state so input signals must not be applied to the DQ pins.

Write Cycle (2)^{*28} (WE# CLOCK, OE# Low Fixed)

Note 28. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

BYTE# $\geq V_{CC} - 0.2V$ (Word mode) or BYTE# $\leq 0.2V$ (Byte mode)

29. t_{WP} is the interval between write start and write end.

A write starts when all of (CS1#), (CS2), (WE#) and (one or both of LB# and UB#) become active.

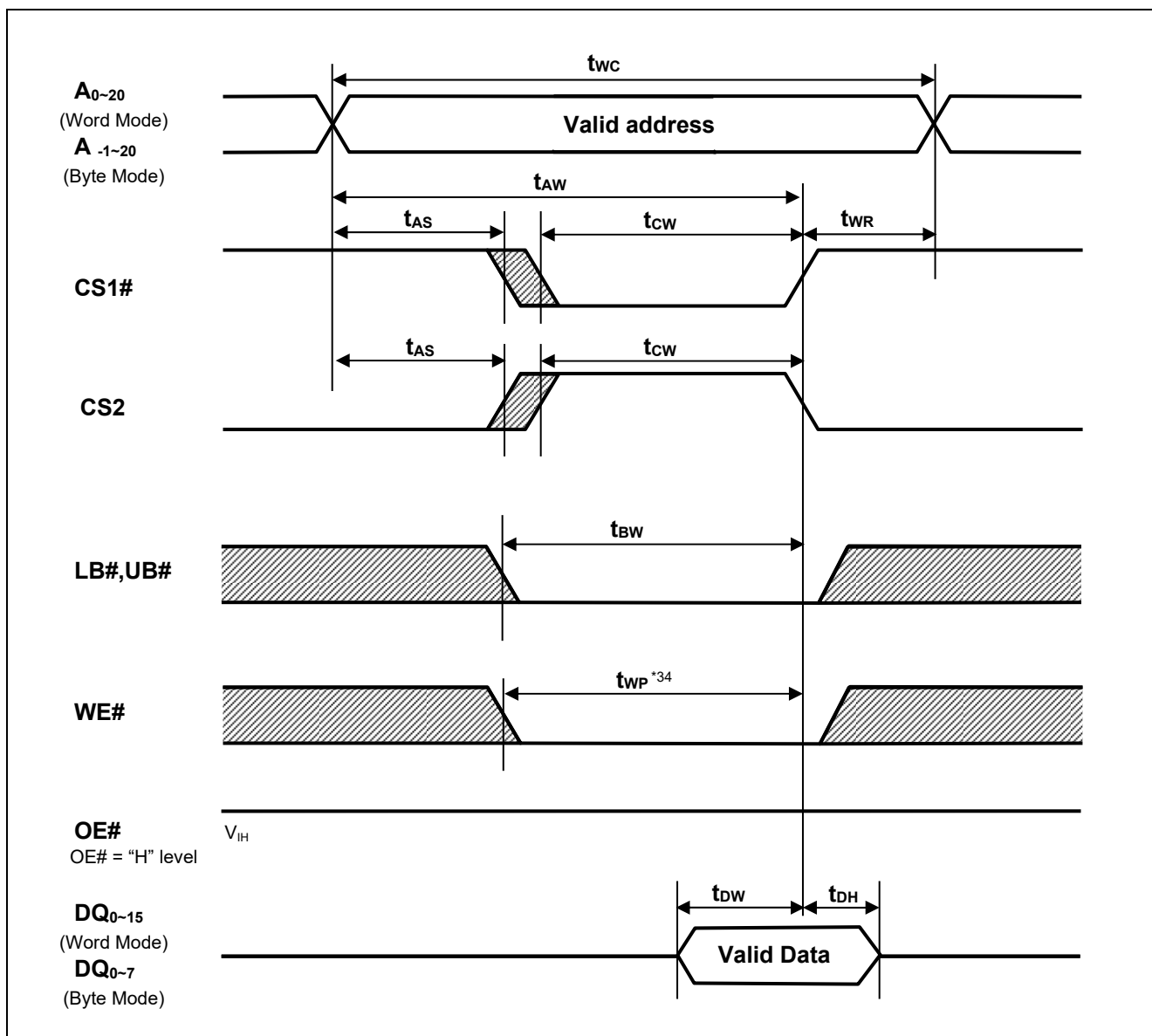
A write is performed during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

A write ends when any of (CS1#), (CS2), (WE#) or (one or both of LB# and UB#) becomes inactive.

30. t_{WHZ} is defined as the time when the DQ pins enter a high-impedance state and are not referred to the DQ levels.

31. This parameter is sampled and not 100% tested.

32. During this period, DQ pins are in the output state so input signals must not be applied to the DQ pins.

Write Cycle (3)^{*33} (CS1#, CS2 CLOCK)

Note 33. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

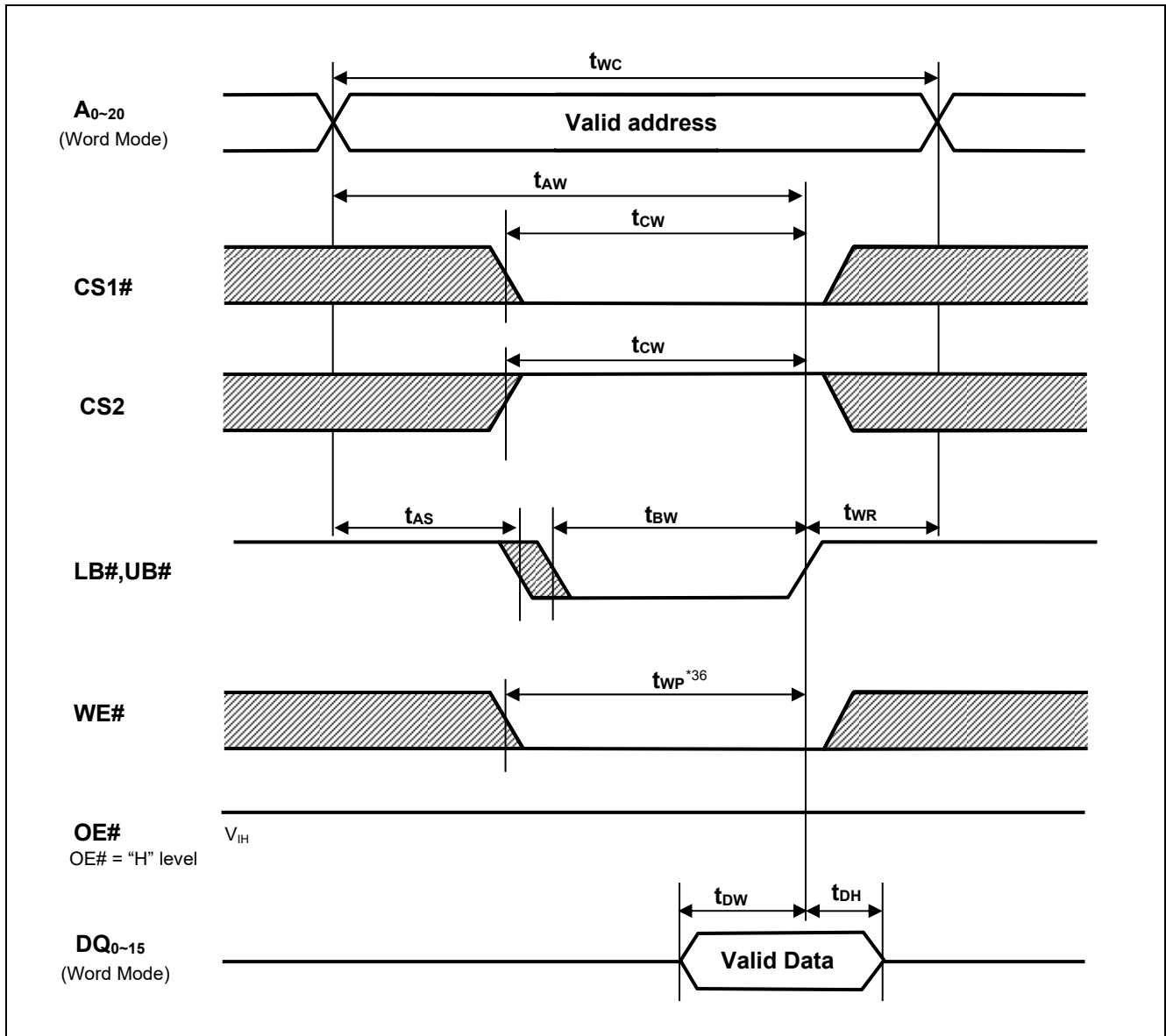
BYTE# $\geq V_{CC} - 0.2V$ (Word mode) or BYTE# $\leq 0.2V$ (Byte mode)

34. t_{WP} is the interval between write start and write end.

A write starts when all of (CS1#), (CS2), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

A write ends when any of (CS1#), (CS2), (WE#) or (one or both of LB# and UB#) becomes inactive.

Write Cycle (4)^{*35} (LB#, UB# CLOCK, Word Mode)

Note 35. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

BYTE# $\geq V_{CC} - 0.2V$ (Word mode)

36. t_{WP} is the interval between write start and write end.

A write starts when all of (CS1#), (CS2), (WE#) and (one or both of LB# and UB#) become active.

A write is performed during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#.

A write ends when any of (CS1#), (CS2), (WE#) or (one or both of LB# and UB#) becomes inactive.

Low V_{CC} Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions*37,38	
V _{CC} for data retention	V _{DR}	1.5	—	3.6	V	Vin ≥ 0V (1) CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V or (3) LB# = UB# ≥ V _{CC} -0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V	
Data retention current	I _{CCDR}	—	0.6*39	4	μA	~+25°C	Vin ≥ 0V (1) CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V or (3) LB# = UB# ≥ V _{CC} -0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V
		—	1*40	6	μA	~+40°C	
		—	4*41	12	μA	~+70°C	
		—	8*42	18	μA	~+85°C	
Chip deselect time to data retention	t _{CDR}	0	—	—	ns	See retention waveform.	
Operation recovery time	t _R	5	—	—	ms		

Note 37. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.

BYTE# $\geq V_{CC} - 0.2V$ or BYTE# $\leq 0.2V$

38. CS2 controls address buffer, WE# buffer, CS1# buffer, OE# buffer, LB# buffer, UB# buffer and DQ buffer.

If CS2 controls data retention mode, V_{in} levels (address, WE#, CS1#, OE#, LB#, UB#, DQ) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be $CS2 \geq V_{CC}-0.2V$ or $CS2 \leq 0.2V$.

The other inputs levels (address, WE#, OE#, LB#, UB#, DQ) can be in the high-impedance state.

39. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=25^{\circ}C$), and not 100% tested.

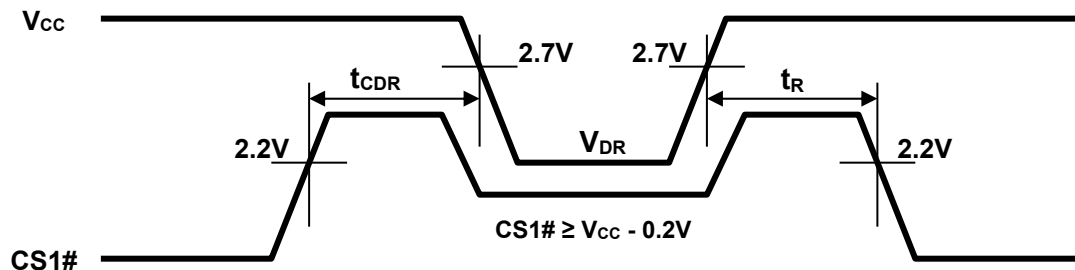
40. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=40^{\circ}C$), and not 100% tested.

41. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=70^{\circ}C$), and not 100% tested.

42. Typical parameter indicates the value for the center of distribution at 3.0V ($T_a=85^{\circ}C$), and not 100% tested.

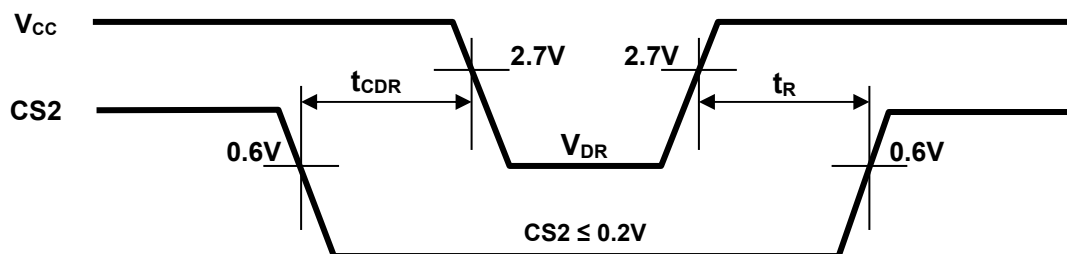
Low Vcc Data Retention Timing Waveforms (CS1# controlled)*43

CS1# Controlled



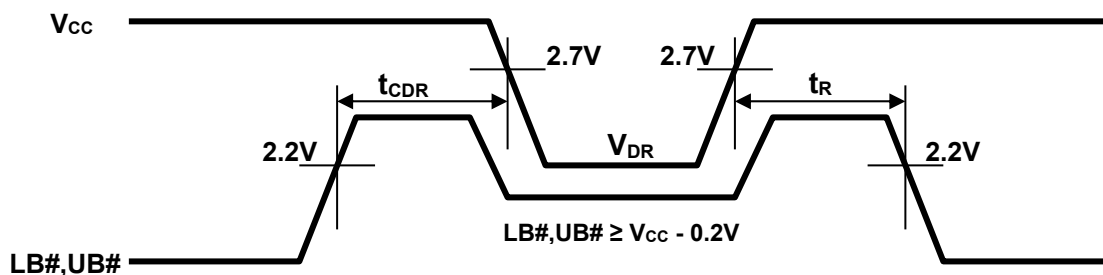
Low Vcc Data Retention Timing Waveforms (CS2 controlled)*43

CS2 Controlled



Low Vcc Data Retention Timing Waveforms (LB#,UB# controlled, Word Mode)*44

LB#,UB# Controlled



Note 43. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.
 BYTE# $\geq V_{CC} - 0.2V$ or BYTE# $\leq 0.2V$

44. BYTE# pin supported by only 48pin TSOP (I) and 52pin μ TSOP (II) types.
 BYTE# $\geq V_{CC} - 0.2V$ (Word mode)

Revision History	RMLV3216A Series Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	2018.12.26	—	First Edition issued
2.00	2024.04.24	P.5,13	Changed maximum value of I_{SB1} and I_{CCDR} : I_{SB1} = from 17 μ A to 12 μ A@70°C, I_{SB1} = from 24 μ A to 18 μ A@85°C I_{CCDR} = from 17 μ A to 12 μ A@70°C, I_{CCDR} = from 24 μ A to 18 μ A@85°C

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